

### 1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at [http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die\\_Broc.pdf](http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die_Broc.pdf) is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at [www.analog.com/AD574](http://www.analog.com/AD574)

### 2.0 Part Number. The complete part number(s) of this specification follow:

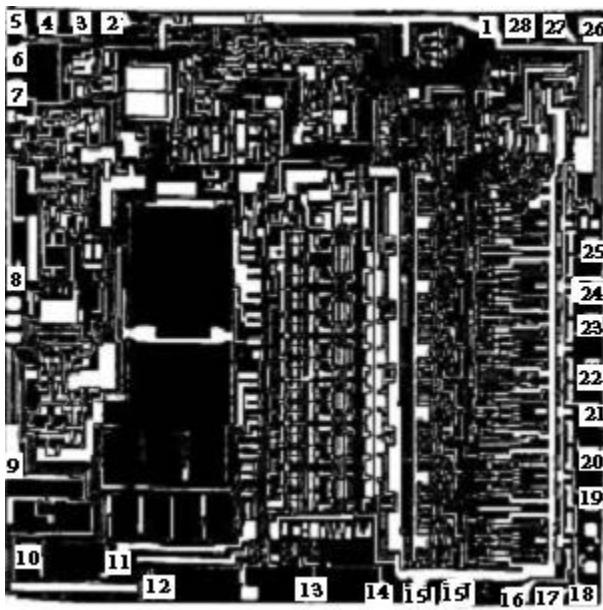
Part Number	Description
AD574-000C	12-Bit-ADC with Microprocessor Interface
AD574R000C	Radiation Tested 12-Bit-ADC with Microprocessor Interface

### 3.0 Die Information

#### 3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization
179 x 180	19 mil ± 2 mil	Al/Cu

#### 3.2 Die Picture



1 $V_{\text{LOGIC}}$	28 STATUS
2 $12/8$	27 DB11
3 $\overline{\text{CS}}$	26 DB10
4 $A_0$	25 DB9
5 $R/\overline{\text{C}}$	24 DB8
6 CE	23 DB7
7 $V_{\text{CC}}$	22 DB6
8 $\text{REF}_{\text{OUT}}$	21 DB5
9 AC	20 DB4
10 $\text{REF}_{\text{IN}}$	19 DB3
11 $V_{\text{EE}}$	18 DB2
12 BIP OFF	17 DB1
13 $10V_{\text{IN}}$	16 DB0
14 $20V_{\text{IN}}$	15 DC

ASD0012706

Rev. H

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### 3.3 Absolute Maximum Ratings

$V_{CC}$ to Digital Common.....	0 to +16.5V dc
$V_{EE}$ to Digital Common.....	0 to -16.5V dc
$V_{LOG}$ to Digital Common.....	0 to +7V dc
Analog to Digital Common.....	$\pm 1V$ dc
Control Inputs ( $\overline{CE}$ , $\overline{CS}$ , $A_0$ , 12/8, R/ $\overline{C}$ ) to Digital Common.....	-0.5V dc to $V_{LOG}+0.5V$ dc
Analog Inputs (REF IN, BIP OFF, 10 $V_{IN}$ ) to Analog Common.....	$V_{EE}$ to $V_{CC}$
20 $V_{IN}$ Analog Input Voltage to Analog Common .....	$\pm 24V$ dc
$V_{REF OUT}$ .....	Indefinite short to common, 10mS
.....	short to $V_{CC}$
Storage Temperature .....	-65°C to +150°C
Junction Temperature ( $T_J$ ).....	+175°C
Operating Temperature Range.....	-55°C to +125°C

### 4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Sample Size and Qual Acceptance Criteria – 10/0
- (b) Qual Sample Package – Ceramic DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

**Table I-Dice Electrical Characteristics**

Parameter	Symbol	Conditions 1/	Limit Min	Limit Max	Units
Power Supply Current From $V_{LOG}$	$I_{LOG}$			40	mA
Power Supply Current From $V_{CC}$	$I_{CC}$			5	mA
Power Supply Current From $V_{EE}$	$I_{EE}$		-30		mA
Resolution			12		Bits
Integral Linearity Error Differential Linearity Error (Minimum Resolution For Which No Missing Codes Guaranteed)	ILE DLE		-0.5	0.5	LSB
			12		Bits
Unipolar Offset Voltage Error	$V_{IO}$		-2.0	2.0	LSB

Table I – Dice Electrical Characteristics (Continued)

Parameter	Symbol	Conditions 1/	Limit Min	Limit Max	Units
Bipolar Offset Voltage Error	B <sub>Z</sub>		-4.0	4.0	LSB
Gain Error	ΔA <sub>E</sub>	With 50Ω resistor from REF OUT to REF IN		.25	% of F.S.
Power Supply Sensitivity (Maximum Change In Full Scale Calibration)	+P <sub>SS1</sub>	+13.5V ≤ V <sub>CC</sub> ≤ +16.5V	-1.0	1.0	LSB
	+P <sub>SS2</sub>	+11.4V ≤ V <sub>CC</sub> ≤ +12.6V			
	+P <sub>SS3</sub>	+4.5V ≤ V <sub>LOG</sub> ≤ + 5.5V	-0.5	0.5	
	-P <sub>SS1</sub>	-16.5V ≤ V <sub>EE</sub> ≤ -13.5V	-1.0	1.0	
	-P <sub>SS2</sub>	-12.6V ≤ V <sub>EE</sub> ≤ -11.4V			
Input Impedance	Z <sub>IN</sub>	10V span	3	7	kΩ
		20V span	6	14	
Internal Reference Voltage	V <sub>REF</sub>	2/	9.98	10.02	V
Input Voltage (CE, $\overline{CS}$ , 12/8, R/ $\overline{C}$ , A <sub>0</sub> ) 3/	V <sub>IH</sub>	Logic "1"	2.0	5.5	V
	V <sub>IL</sub>	Logic "0"	-0.5	0.8	
Input Current	I <sub>IN</sub>		-20	+20	μA
Output Voltage (DB11-DB0, STS)	V <sub>OL</sub>	Logic "0", I <sub>SINK</sub> = +1.6mA		0.4	V
Output Voltage (DB11-DB0)	V <sub>OH</sub>	Logic "1", I <sub>SOURCE</sub> = +500μA	2.4		V
High Impedance State Output Current	I <sub>Z</sub>	High-Z state, DB11 – DB0 only	-20	+20	μA

## Table I Notes:

- 1/ V<sub>CC</sub> = ±15V, V<sub>LOG</sub> = +5V, V<sub>EE</sub> = -15V, T<sub>A</sub> = 25°C, unless otherwise specified.  
2/ The reference voltage external load current shall be a constant dc and shall not exceed 1.5 mA. Reference should be buffered for operation of ±12V supplies. External load should not change during conversion.  
3/ 12/8 is not TTL compatible and must be hard wired to V<sub>LOG</sub> or digital ground.

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**Table II - Electrical Characteristics for Qual Samples**

Parameter	Symbol	Conditions 1/	Sub-groups	Limit Min	Limit Max	Units
Power Supply Current From $V_{LOG}$	$I_{LOG}$		1, 2, 3		40	mA
		M, D, L, R 5/	1		40	
Power Supply Current From $V_{CC}$	$I_{CC}$		1, 2, 3		5	
		M, D, L, R 5/	1		5	
Power Supply Current From $V_{EE}$	$I_{EE}$		1, 2, 3	-30		
		M, D, L, R 5/	1	-30		
Integral Linearity Error	ILE		1	-0.5	0.5	LSB
			2, 3	-1.0	1.0	
		M, D, L, R 5/	1	-1.0	1.0	
Differential Linearity Error (Minimum Resolution For Which No Missing Codes Guaranteed) 6/	DLE		1	12		Bits
			2, 3	12		
Unipolar Offset Voltage Error	$V_{IO}$	Using internal reference	1	-2.0	2.0	LSB
		M, D, L, R 5/	1	-3.0	3.0	
Unipolar Offset Drift 6/	$\frac{\Delta V_{IO}}{\Delta T}$	Using internal reference	2, 3	-1.0	1.0	
Bipolar Offset Voltage Error	$B_Z$	Using internal reference	1	-4.0	4.0	
		M, D, L, R 5/	1	-5.0	5.0	
Bipolar Zero Offset Drift 6/	$\frac{\Delta B_Z}{T}$	Using internal reference	2, 3	-2.0	+2.0	
Gain Error	$\Delta A_E$	With 50Ω resistor from REF OUT to REF IN	1		.25	% of F.S.
		M, D, L, R 5/	1		.35	
Gain Error Drift 6/	$\frac{\Delta A_E}{\Delta T}$	Using internal reference	2, 3	-25.0	25.0	ppm/°C
Power Supply Sensitivity (Maximum Change In Full Scale Calibration) 6/	+P <sub>SS1</sub>	+13.5V ≤ V <sub>CC</sub> ≤ +16.5V	1	-1.0	1.0	LSB
	+P <sub>SS2</sub>	+11.4V ≤ V <sub>CC</sub> ≤ +12.6V				
	+P <sub>SS3</sub>	+4.5V ≤ V <sub>LOG</sub> ≤ +5.5V	1	-0.5	0.5	
	-P <sub>SS1</sub>	-16.5V ≤ V <sub>EE</sub> ≤ -13.5V	1	-1.0	1.0	
	-P <sub>SS2</sub>	-12.6V ≤ V <sub>EE</sub> ≤ -11.4V				
Input Impedance 6/	$Z_{IN}$	10V span	1	3	7	kΩ
		20V span	1	6	14	

Table II - Electrical Characteristics for Qual Samples

Parameter	Symbol	Conditions 1/	Sub- groups	Limit Min	Limit Max	Units
Output Voltage (DB11-DB0, STS) 6/	$V_{OL}$	Logic "0", $T_A = +25^\circ\text{C}$ , $I_{SINK} = +1.6\text{mA}$	1, 2, 3		40	mA
Output Voltage (DB11-DB0) 6/	$V_{OH}$	Logic "1", $T_A = +25^\circ\text{C}$ , $I_{SOURCE} = +500\mu\text{A}$	1	2.4		V
High Impedance State Output Current 6/	$I_Z$	High-Z state, $T_A = +25^\circ\text{C}$ , DB11-DB0 only	1	-20	+20	$\mu\text{A}$
Low $R/\bar{C}$ Pulse Width 4/ 6/	$t_{HRL}$		9	250		ns
STS Delay from $R/\bar{C}$ 4/ 6/	$t_{DS}$		9		600	ns
Data Valid After $R/\bar{C}$ Low 4/ 6/	$t_{HDR}$		9		25	ns
STS Delay After Valid Data 4/ 6/	$t_{HS}$		9	300	1000	ns
High $R/\bar{C}$ Pulse Width 6/	$t_{HRH}$		9	300		ns
Data Access Time 6/	$t_{DDR}$		9		250	ns
STS Delay from CE 6/	$t_{DSC}$		9		350	ns
CE Pulse Width 6/	$t_{HEC}$		9	300		ns
Conversion Time 6/	$t_C$	8-bit cycle	9	10	24	$\mu\text{s}$
		12-bit cycle	9	15	35	
Access Time (from CE) 6/	$t_{DD}$		9		200	ns

Table II Notes:

- 1/  $V_{CC} = \pm 15\text{V}$ ,  $V_{LOG} = +5\text{V}$ ,  $V_{EE} = -15\text{V}$ ,  $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$ , unless otherwise specified.
- 2/ The reference voltage external load current shall be a constant dc and shall not exceed 1.5 mA. Reference should be buffered for operation of  $\pm 12\text{V}$  supplies. External load should not change during conversion.
- 3/ 12/8 is not TTL compatible and must be hard wired to  $V_{LOG}$  or digital ground.
- 4/ Subgroups 10 and 11, if not tested, shall be guaranteed to the specified limits.
- 5/ Tested at 100Krad
- 6/ Not Tested Post Irradiation.

**Table III - Delta Parameter Table**

Parameter	Symbol	Sub-groups	Post Burn In Limit		Post Life Test Limit		Life Test Delta	Units
			Min	Max	Min	Max		
Unipolar Offset Voltage Error	Uni $V_{IO}$	1	-2.0	2.0	-2.5	2.5	$\pm 0.5$	LSB
Bipolar Offset Voltage Error	Bpze	1	-4.0	4.0	-5.0	5.0	$\pm 1.0$	LSB
Gain Error	$A_E$	1	-0.25	0.25	-0.25	0.35	$\pm .10$	%FSR

**5.0 Life Test/Burn-In Information**

- 5.1 HTRB is not applicable for this drawing.  
 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.  
 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	04-Oct-2001
B	Update web address	Jan. 25, 2002
C	Update web address. Add Radiation limits and part number.	4-Mar-03
D	Update 1.0 Scope description.	2 Aug. 2007
E	Update header/footer & add to 1.0 Scope description.	Feb. 14, 2008
F	Remove reference to condition 5/ note on Table I & add Junction Temperature ( $T_J$ ).... +175°C & Operating Temperature Range....-55°C to +125°C to Section 3.3-Absolute Max. Ratings	March 27, 2008
G	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	6-JUN-2009
H	Updated Font and Font Size to Standardize to ADI format	20-Sep-2011



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